

Notice of References Cited

Application/Control No.

09/603,941

Applicant(s)/Patent Under Review

Bao et al.

Examiner

George C. Eckert II

Art Unit

2815

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	Document Number Country Code-Number-Kind Code	Date MM-YYYY ¹	Name	Classification ²	
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C	5,321,102	6/1994	Loy et al.	525	474
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N	4-4-228415	8/1992	Japan	Baney et al.	C01B	33/12
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NON-PATENT DOCUMENTS

	Include, as applicable: Author, Title, Date, Publisher, Edition or Volume, Pertinent Pages
U	Allman et al., The Material Characteristics of a New Methyl-Phenyl Silsesquioxane Spin-On Glass for Use in a Global Non-Etchback Interconnect Planarization Process, June 1991, IEEE, VMIC Conference, pp. 373-75.
V	Jeng et al., Highly Porous Interlayer Dielectric For Interconnect Capacitance Reduction, 1995, Symposium on VLSI Technology Digest of Technical Papers, pp. 61-62.
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¹ A copy of this reference is not being furnished with this Office action. See MPEP § 707.05(a).¹ Dates in MM-YYYY format are publication dates.² Classifications may be U.S. or foreign.